



DMTH6016LPD

60V 175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	19mΩ @ V _{GS} = 10V	33.2A
	$28m\Omega @ V_{GS} = 4.5V$	28A

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production –
 Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Data Sheet (<u>DMTH6016LPDQ</u>)

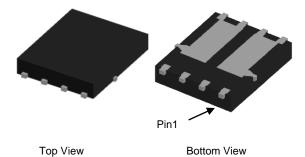
Description and Applications

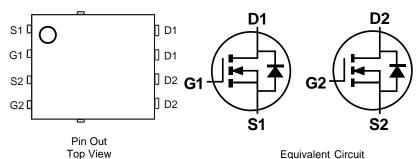
This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Engine Management Systems
- Body Control Electronics
- DCDC Converters

Mechanical Data

- Case: PowerDI[®]5060-8 (Type C)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)





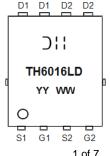
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH6016LPD-13	PowerDI5060-8 (Type C)	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



⊃¦¦ = Manufacturer's Marking TH6016LD = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 18 = 2018) WW = Week (01 to 53)

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Document number: DS39224 Rev. 3 - 2

1 of 7 www.diodes.com



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	60	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current (Note 6)	$T_C = +25$ °C $T_C = +100$ °C	I _D	33.2 23.7	А
Continuous Drain Current (Note 5) $T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$		I _D	9.2 6.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	50	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	31	Α	
Avalanche Current, L = 0.1mH	I _{AS}	15.3	Α	
Avalanche Energy, L = 0.1mH	E _{AS}	11.7	mJ	

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	58	°C/W
Total Power Dissipation (Note 6)	P_D	37.5	W
Thermal Resistance, Junction to Case (Note 6)	R _{eJC}	4	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage		_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		_	14.5	19	mΩ	$V_{GS} = 10V, I_D = 10A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		20.9	28	11112	$V_{GS} = 4.5V, I_D = 6A$	
Diode Forward Voltage	V_{SD}		0.7	1.2	V	V _{GS} = 0V, I _S = 20A	
DYNAMIC CHARACTERISTICS (Note 8)				•	•	•	
Input Capacitance	Ciss	_	864	_	pF		
Output Capacitance	Coss	_	282	_	pF	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	27	_	pF	T = TIVIHZ	
Gate Resistance	R_g	_	1.3	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	8.4	_	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	_	17	_	nC	V _{DS} = 30V, I _D = 10A	
Gate-Source Charge	Q _{gs}	_	3.1	_	nC		
Gate-Drain Charge	Q _{gd}	_	4.3	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	3.4	_	ns		
Turn-On Rise Time	t _R	_	5.2	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 10A, R_{g} = 6\Omega$	
Turn-Off Delay Time	t _{D(OFF)}	_	13	_	ns		
Turn-Off Fall Time	t _F	_	7	_	ns		
Body Diode Reverse Recovery Time	t _{RR}	-	22	_	ns		
Body Diode Reverse Recovery Charge	Q_{RR}	_	11	_	nC	$I_F = 10A$, di/dt = 100A/ μ s	

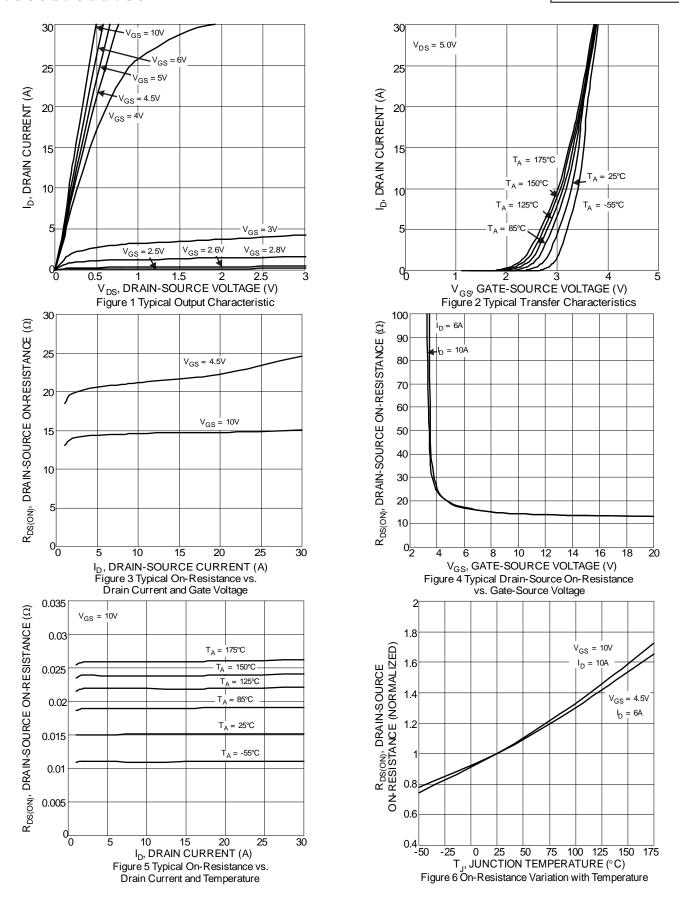
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:



March 2018

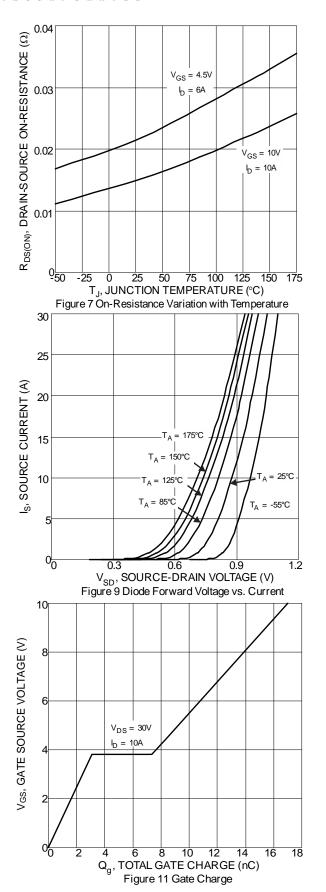
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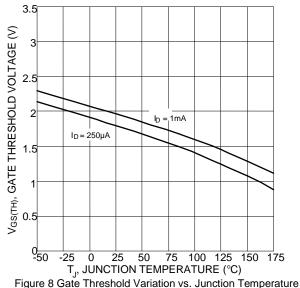


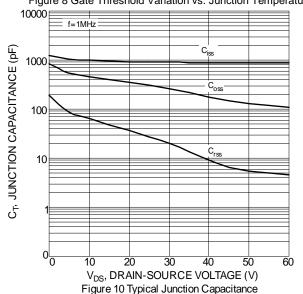


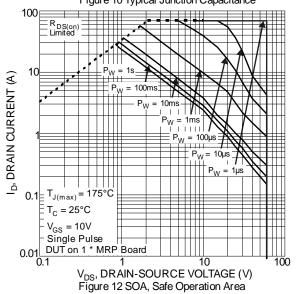




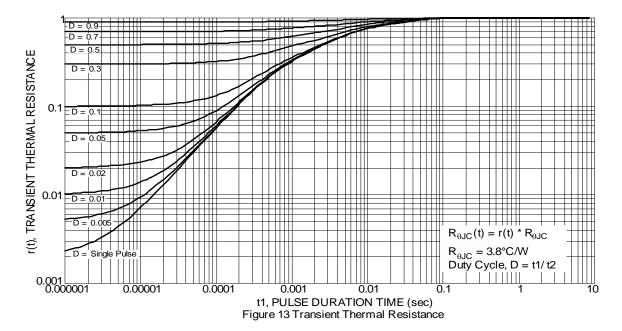










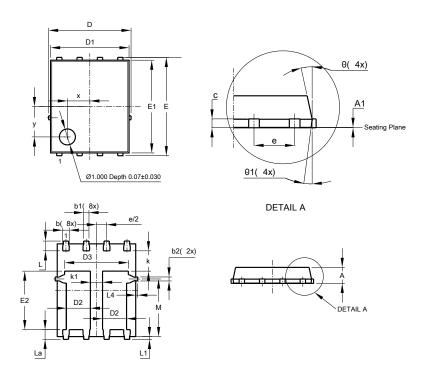




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type C)

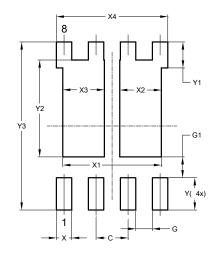


PowerDI5060-8 (Type C)					
Dim	Min				
Α	0.90	1.10	1.00		
A1	0	0.05	0.02		
b	0.33	0.51	0.41		
b1	0.300	0.366	0.333		
b2	0.20	0.35	0.25		
С	0.23	0.33	0.277		
D	ţ	5.15 BSC	;		
D1	4.85	4.95	4.90		
D2	1.40	1.60	1.50		
D3	-	-	3.98		
Е	6.15 BSC				
E1	5.75	5.85	5.80		
E2	3.56	3.76	3.66		
е	1.27BSC				
k	-	-	1.27		
k1	0.56	-	-		
L	0.51	0.71	0.61		
La	0.51	0.71	0.61		
L1	0.05	0.20	0.175		
L4	-	-	0.125		
M	3.50	3.71	3.605		
Х	-	-	1.400		
у	-	-	1.900		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type C)



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	3.910
X2	1.650
Х3	1.650
X4	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610



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